

# 100V, 110A, 4.8mΩ N-channel Power SGT MOSFET

## JMSH1005PG

### Features

- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- 100% UIS Tested
- 100%  $\Delta V_{DS}$  Tested
- Halogen-free; RoHS-compliant

### Applications

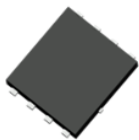
- Load Switch
- PWM Application
- Power Management

### Product Summary

| Parameters                     | Value | Unit |
|--------------------------------|-------|------|
| $V_{DSS}$                      | 100   | V    |
| $V_{GS(th\_Typ)}$              | 2.9   | V    |
| $I_D(@V_{GS}=10V)$             | 110   | A    |
| $R_{DS(ON\_Typ)}(@V_{GS}=10V)$ | 4.8   | mΩ   |

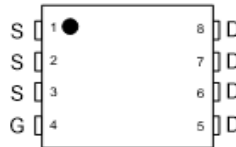
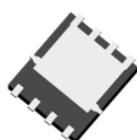


Top View

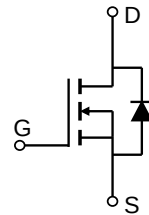


PDFN5X6-8L

Bottom View



Pin Assignment



Schematic Diagram

### Ordering Information

| Device        | Marking | MSL | Form      | Package    | Reel(pcs) | Per Carton (pcs) |
|---------------|---------|-----|-----------|------------|-----------|------------------|
| JMSH1005PG-13 | SH1005P | 1   | Tape&Reel | PDFN5x6-8L | 5000      | 50000            |

### Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

| Symbol         | Parameter                                     | Value                                                 | Unit             |
|----------------|-----------------------------------------------|-------------------------------------------------------|------------------|
| $V_{DS}$       | Drain-to-Source Voltage                       | 100                                                   | V                |
| $V_{GS}$       | Gate-to-Source Voltage                        | $\pm 20$                                              | V                |
| $I_D$          | Continuous Drain Current                      | $T_C = 25^\circ\text{C}$<br>$T_C = 100^\circ\text{C}$ | A                |
| $I_{DM}$       | Pulsed Drain Current <sup>(1)</sup>           | Refer to Fig.4                                        | A                |
| $E_{AS}$       | Single Pulsed Avalanche Energy <sup>(2)</sup> | 485                                                   | mJ               |
| $P_D$          | Power Dissipation                             | $T_C = 25^\circ\text{C}$<br>$T_C = 100^\circ\text{C}$ | W                |
| $T_J, T_{STG}$ | Junction & Storage Temperature Range          | -55 to 150                                            | $^\circ\text{C}$ |

### Thermal Characteristics

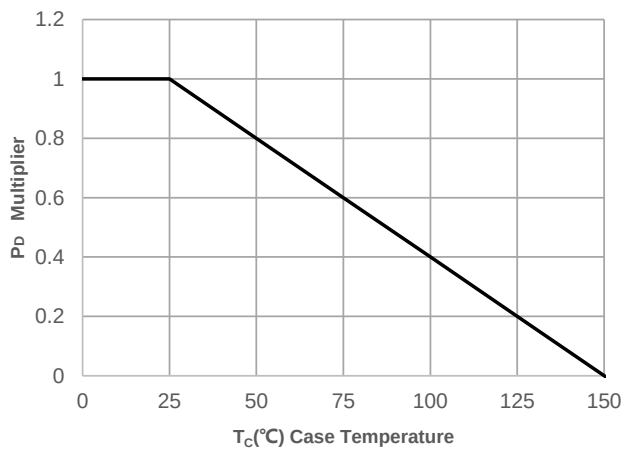
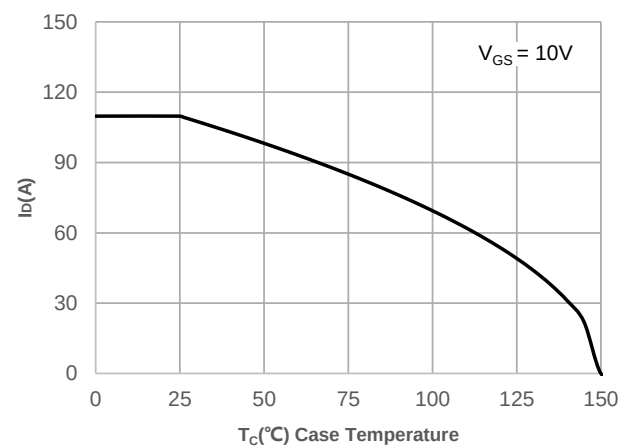
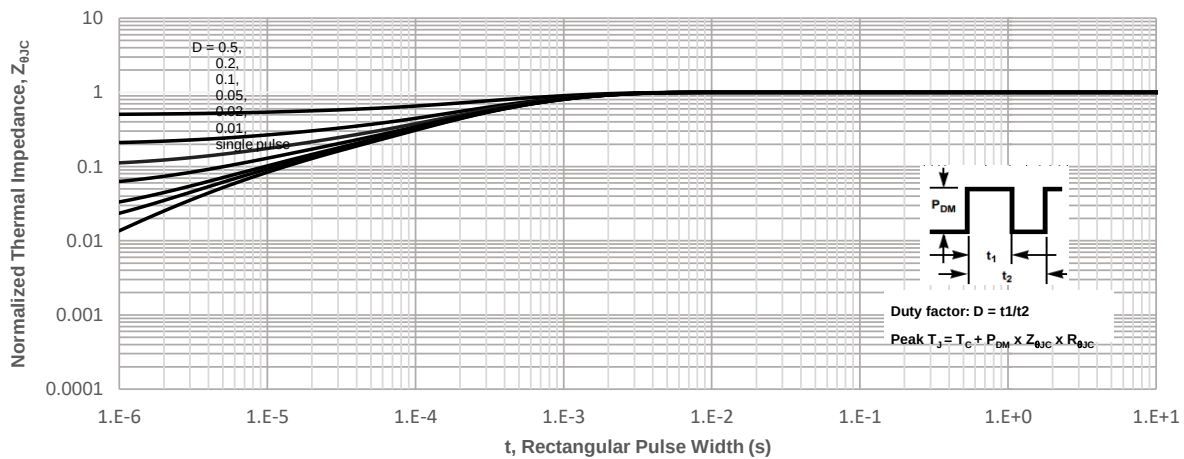
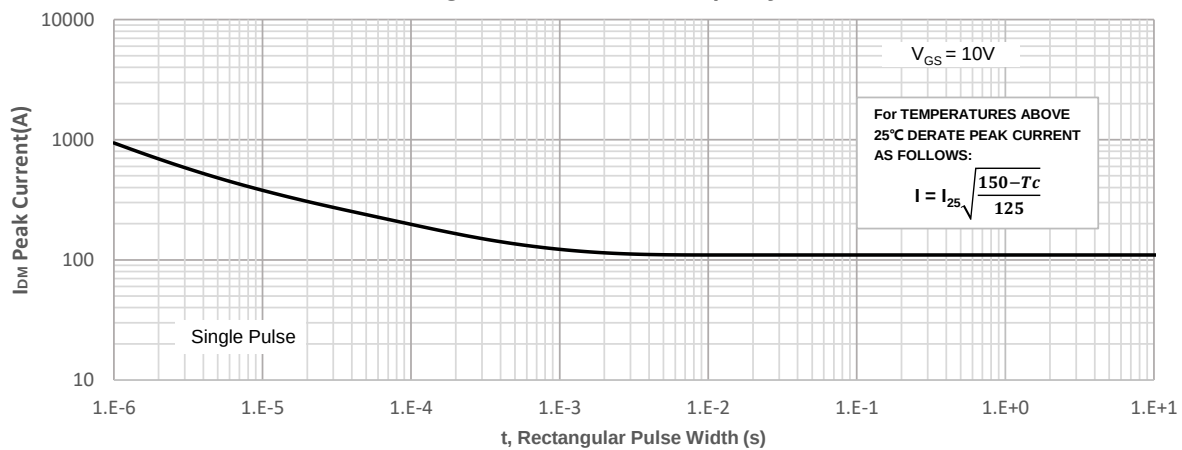
| Symbol          | Parameter                                              | Max | Unit               |
|-----------------|--------------------------------------------------------|-----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient <sup>(3)</sup> | 77  | $^\circ\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case                   | 0.8 |                    |

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

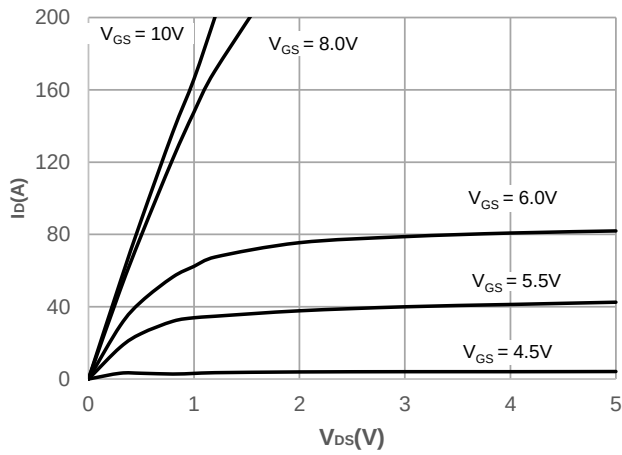
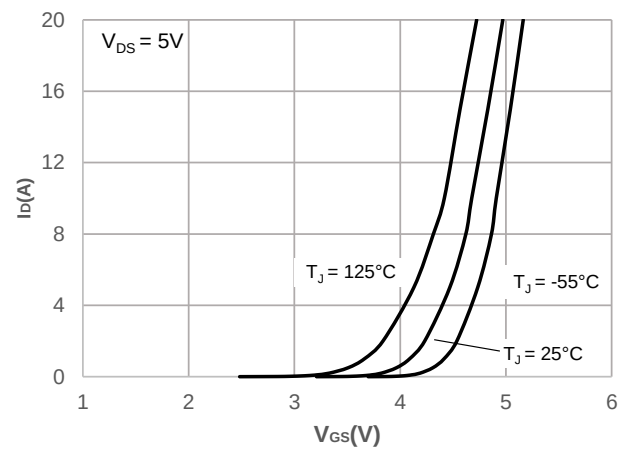
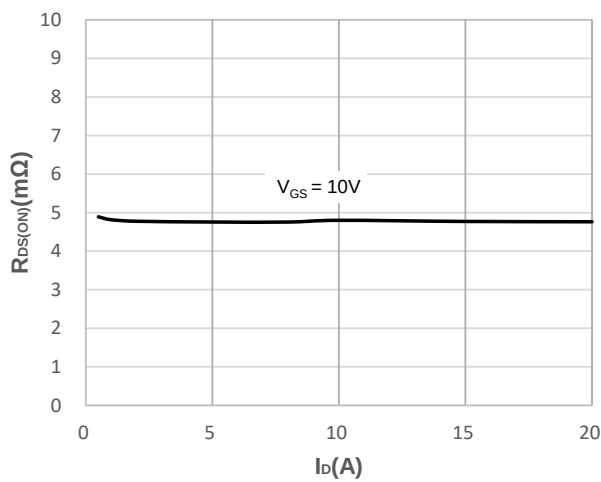
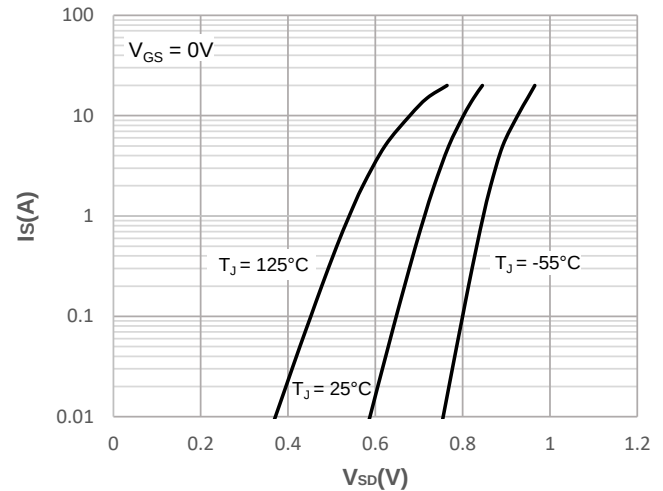
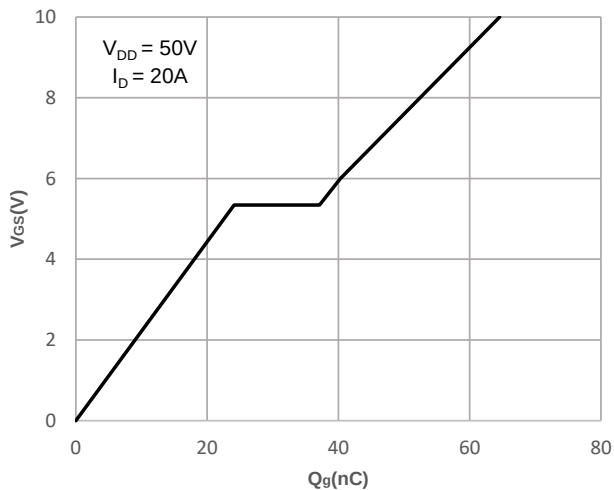
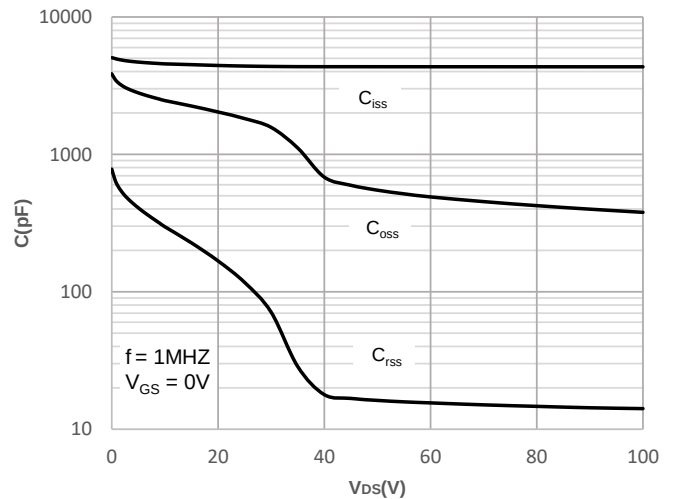
| Symbol                     | Parameter                                        | Conditions                                                                                    | Min. | Typ. | Max. | Unit |
|----------------------------|--------------------------------------------------|-----------------------------------------------------------------------------------------------|------|------|------|------|
| Off Characteristics        |                                                  |                                                                                               |      |      |      |      |
| V <sub>(BR)DSS</sub>       | Drain-Source Breakdown Voltage                   | I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V                                                  | 100  | -    | -    | V    |
| I <sub>DSS</sub>           | Zero Gate Voltage Drain Current                  | V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V                                                   | -    | -    | 1.0  | μA   |
| I <sub>GSS</sub>           | Gate-Body Leakage Current                        | V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V                                                  | -    | -    | ±100 | nA   |
| On Characteristics         |                                                  |                                                                                               |      |      |      |      |
| V <sub>GS(th)</sub>        | Gate Threshold Voltage                           | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                    | 2.1  | 2.9  | 3.8  | V    |
| R <sub>DS(ON)</sub>        | Static Drain-Source ON-Resistance <sup>(4)</sup> | V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A                                                   | -    | 4.8  | 6.2  | mΩ   |
| Dynamic Characteristics    |                                                  |                                                                                               |      |      |      |      |
| R <sub>g</sub>             | Gate Resistance                                  | f = 1MHz                                                                                      | -    | 1.7  | -    | Ω    |
| C <sub>iss</sub>           | Input Capacitance                                | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 50V,<br>f = 1MHz                                      | 3103 | 4344 | 5865 | pF   |
| C <sub>oss</sub>           | Output Capacitance                               |                                                                                               | 392  | 549  | 741  | pF   |
| C <sub>rss</sub>           | Reverse Transfer Capacitance                     |                                                                                               | 12   | 16   | 22   | pF   |
| Q <sub>g</sub>             | Total Gate Charge                                | V <sub>GS</sub> = 0 to 10V<br>V <sub>DS</sub> = 50V, I <sub>D</sub> = 20A                     | 46   | 65   | 87   | nC   |
| Q <sub>gs</sub>            | Gate Source Charge                               |                                                                                               | 17   | 24   | 33   | nC   |
| Q <sub>gd</sub>            | Gate Drain("Miller") Charge                      |                                                                                               | 9    | 13   | 18   | nC   |
|                            |                                                  |                                                                                               |      |      |      |      |
| Switching Characteristics  |                                                  |                                                                                               |      |      |      |      |
| t <sub>d(on)</sub>         | Turn-On DelayTime                                | V <sub>GS</sub> = 10V, V <sub>DD</sub> = 50V<br>I <sub>D</sub> = 20A, R <sub>GEN</sub> = 6.2Ω | -    | 22   | -    | ns   |
| t <sub>r</sub>             | Turn-On Rise Time                                |                                                                                               | -    | 29   | -    | ns   |
| t <sub>d(off)</sub>        | Turn-Off DelayTime                               |                                                                                               | -    | 50   | -    | ns   |
| t <sub>f</sub>             | Turn-Off Fall Time                               |                                                                                               | -    | 23   | -    | ns   |
| Body Diode Characteristics |                                                  |                                                                                               |      |      |      |      |
| I <sub>S</sub>             | Maximum Continuous Body Diode Forward Current    |                                                                                               | -    | -    | 110  | A    |
| I <sub>SM</sub>            | Maximum Pulsed Body Diode Forward Current        |                                                                                               | -    | -    | 439  | A    |
| V <sub>SD</sub>            | Body Diode Forward Voltage                       | V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A                                                    | -    |      | 1.2  | V    |
| trr                        | Body Diode Reverse Recovery Time                 | I <sub>F</sub> = 20A, di/dt = 100A/us                                                         | 50   | 71   | 95   | ns   |
| Qrr                        | Body Diode Reverse Recovery Charge               |                                                                                               | -    | 185  | -    | nC   |

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2.  $E_{AS}$  condition: Starting  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = 50\text{V}$ ,  $V_{GS} = 10\text{V}$ ,  $R_G = 25\text{ohm}$ ,  $L = 3\text{mH}$ ,  $I_{AS} = 17.99\text{A}$ ,  $V_{DD} = 0\text{V}$  during time in avalanche.
  3.  $R_{\theta JA}$  is measured with the device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  4. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .

## Typical Performance Characteristics

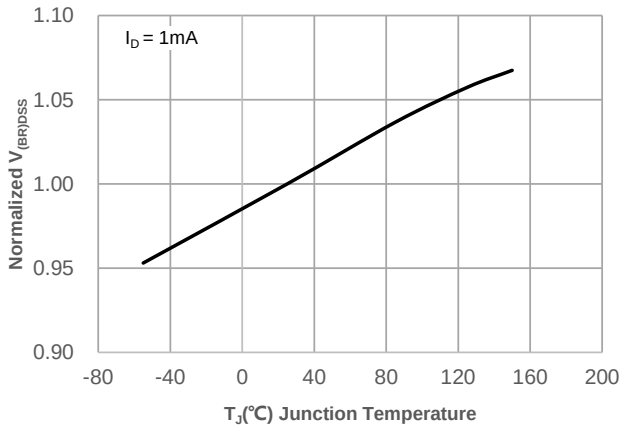
**Figure 1: Power De-rating**

**Figure 2: Current De-rating**

**Figure 3: Normalized Maximum Transient Thermal Impedance**

**Figure 4: Peak Current Capacity**


## Typical Performance Characteristics

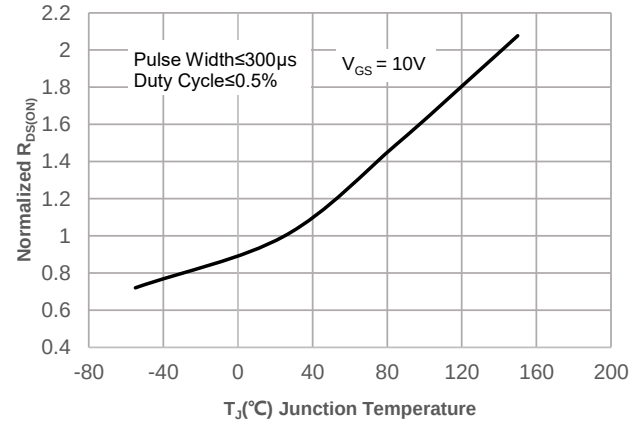
**Figure 5: Output Characteristics**

**Figure 6: Typical Transfer Characteristics**

**Figure 7: On-resistance vs. Drain Current**

**Figure 8: Body Diode Characteristics**

**Figure 9: Gate Charge Characteristics**

**Figure 10: Capacitance Characteristics**


## Typical Performance Characteristics

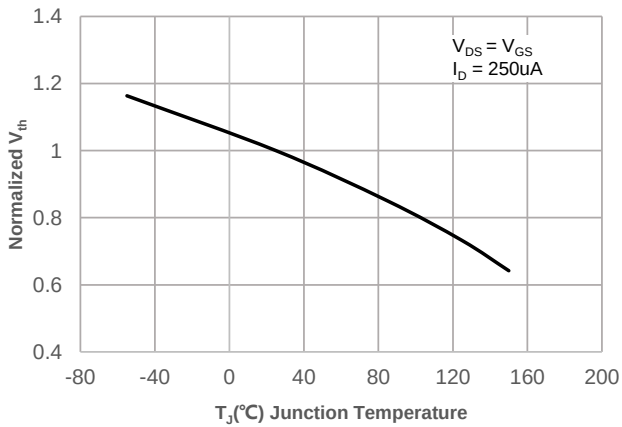
**Figure 11: Normalized Breakdown voltage vs. Junction Temperature**



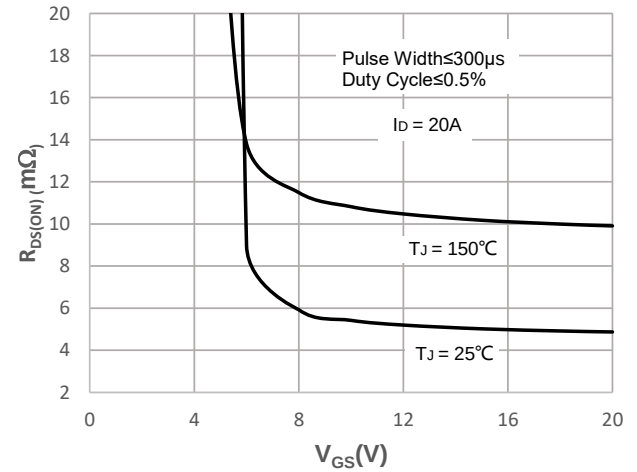
**Figure 12: Normalized on Resistance vs. Junction Temperature**



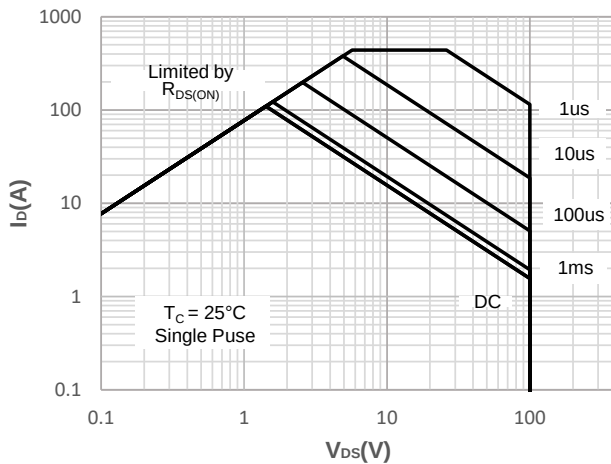
**Figure 13: Normalized Threshold Voltage vs. Junction Temperature**



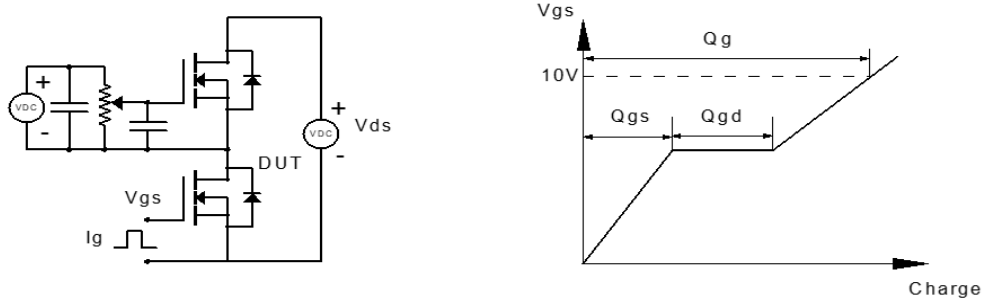
**Figure 14:  $R_{DS(ON)}$  vs.  $V_{GS}$**



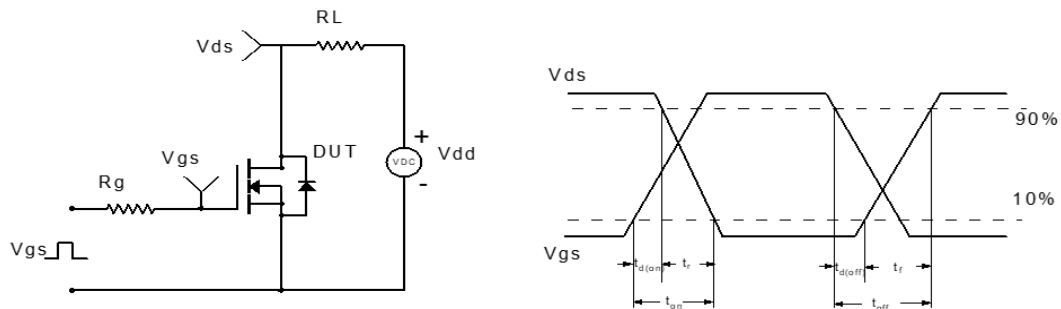
**Figure 15: Maximum Safe Operating Area**



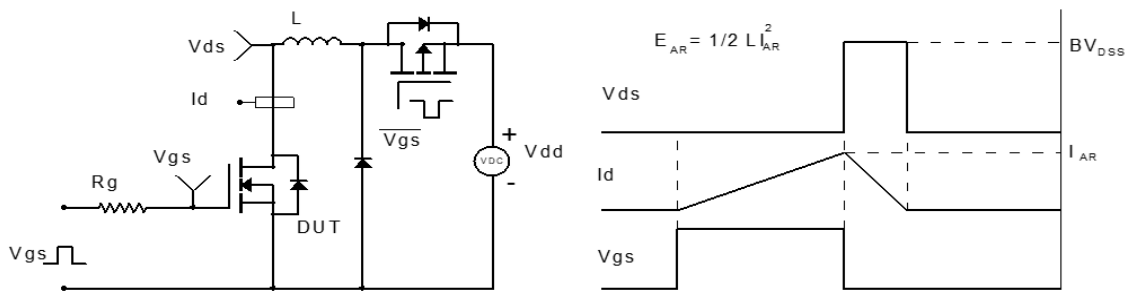
## Test Circuit



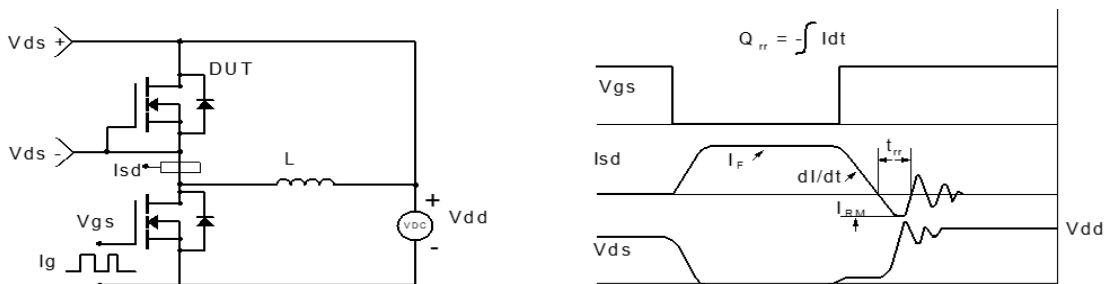
**Figure 1: Gate Charge Test Circuit & Waveform**



**Figure 2: Resistive Switching Test Circuit & Waveform**



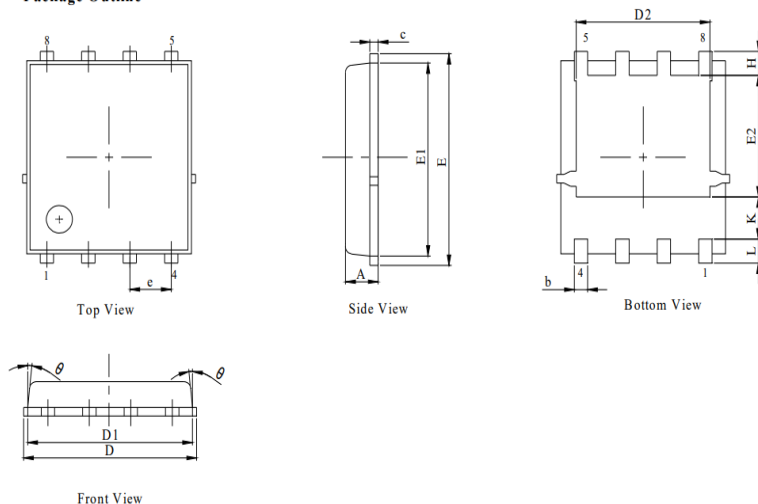
**Figure 3: Unclamped Inductive Switching Test Circuit& Waveform**



**Figure 4: Diode Recovery Test Circuit & Waveform**

## Package Mechanical Data(PDFN5X6-8L )

### Package Outline

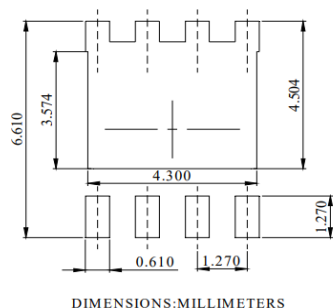


#### NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions D1 and E1 do not include mold flash protrusions or gate burrs.

| DIM. | MILLIMETER |      |      |
|------|------------|------|------|
|      | MIN.       | NOM. | MAX. |
| A    | 0.9        | 1    | 1.15 |
| b    | 0.31       | 0.41 | 0.51 |
| C    | 0.24       | 0.32 | 0.4  |
| D    | 5          | 5.2  | 5.4  |
| D1   | 4.95       | 5.05 | 5.15 |
| D2   | 4          | 4.1  | 4.2  |
| E    | 6.05       | 6.15 | 6.25 |
| E1   | 5.5        | 5.6  | 5.7  |
| E2   | 3.42       | 3.53 | 3.63 |
| e    | 1.27BSC    |      |      |
| H    | 0.6        | 0.7  | 0.8  |
| L    | 0.5        | 0.7  | 0.8  |
| K    | 1.23 REF   |      |      |
| 0    |            |      | 10   |

### Recommended Soldering Footprint



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